

AMENDMENTS

In the Claims

The following is a courtesy copy of the claims indicating that claims 13 – 18 and 21 – 22 are currently withdrawn:

1. (Original) A transistor device having a metallic source electrode, a metallic drain electrode, a metallic gate electrode and a channel in a deposited semiconductor material, the transistor device comprising:

a first layer comprising the metallic gate electrode, a first metal portion of the metallic source electrode and a first metal portion of the metallic drain electrode;

a second layer comprising a second metal portion of the metallic source electrode, a second metal portion of the metallic drain electrode, the deposited semiconductor material and dielectric material between the semiconductor material and the metallic gate electrode; and

a third layer comprising a substrate, wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer.

2. (Original) A transistor device as claimed in claim 1, wherein the metallic source electrode, drain electrode and gate electrode comprise electro-deposited metal.

3. (Previously Presented) A transistor device as claimed in claim 1, wherein the first, second and third layers are each of respective substantially uniform thickness.

4. (Previously Presented) A transistor device as claimed in claim 1, wherein the third layer includes adhesive bonding the passive substrate to the transistor device.

5. (Previously Presented) A transistor device as claimed in claim 1, wherein the first layer has a substantially planar surface comprising substantially planar portions of the source, drain and gate electrodes.

6. (Previously Presented) A transistor device as claimed in claim 1, wherein the deposited semiconductor material comprises organic semiconductor material.

7. (Previously Presented) A transistor device as claimed in claim 1, wherein the deposited semiconductor material comprises indications that it was deposited from liquid.

8. (Previously Presented) A transistor device as claimed in claim 1, wherein the semiconductor material is embedded in the device and overlain by the gate electrode.

9. (Previously Presented) A transistor device as claimed in claim 1 wherein the first layer comprises insulating material separating the gate electrode from the source electrode and the drain electrode.

10. – 11. (Canceled)

12. (Previously Presented) A substrate for a display device comprising a plurality of transistor devices as claimed in claim 1.

13. (Withdrawn) A method for use in forming a transistor device comprising:
(i) forming a transfer layer on a conductive carrier;
(ii) fixing the transfer layer to a substrate; and
(iii) removing the conductive carrier, wherein the transfer layer is formed in step (i) by:

- a) selectively masking the conductive carrier, to expose first, second and third portions of the conductive carrier;
- b) electro-depositing metal onto the first, second and third portions of the conductive carrier to form first, second and third metal portions;
- c) depositing dielectric material over at least the second metal portion;
- d) electro depositing metal on the first and third metal portions; and
- e) depositing semiconductor material over the dielectric layer.

14. (Withdrawn) A method as claimed in claim 13, wherein the step of selectively masking the conductive carrier includes the selective formation of insulating material on portions of the conductive carrier and the retention of the insulating material within the transistor device.

15. (Withdrawn) A method as claimed in claim 13, wherein the transfer layer provides a terminal layer of the device.

16. (Withdrawn) A method as claimed in claim 13, wherein the step of fixing the transfer layer to a substrate portion embeds semiconductor material within the device.

17. (Withdrawn) A method as claimed in claim 13, wherein the semiconductor material deposited in step e) is selectively deposited between the metal deposited in step d).

18. (Withdrawn) A method as claimed in any claim 13, wherein the step e) precedes step d).

19. – 20. (Canceled)

21. (Withdrawn) A method as claimed in claim 13, wherein the step of fixing the transfer layer to the substrate involves the application of a curable adhesive to the substrate, the contacting of the adhesive layer and the transfer layer and the curing of the adhesive.

22. (Withdrawn) A semiconductor device formed using the method as claimed in claim 13.

23. – 24. (Canceled)

25. (Previously Presented) A transistor device having a metallic source electrode, a metallic drain electrode, a metallic gate electrode and a channel in a deposited semiconductor material, the transistor device comprising:

a first upper planar layer comprising the metallic gate electrode, a first metal portion of the metallic source electrode and a first metal portion of the metallic drain electrode;

a second middle planar layer comprising a second metal portion of the metallic source electrode, a second metal portion of the metallic drain electrode, the deposited semiconductor material and dielectric material between the semiconductor material and the metallic gate electrode; and

a third lower planar layer comprising a substrate, wherein first, second and third planar layers are arranged in order such that the second middle layer is positioned between the first upper layer and the third lower layer,

wherein the metallic source electrode, drain electrode and gate electrode comprise electro-deposited metal, the gate electrode occupies only the first upper planar layer and the channel occupies only the second middle planar layer, the metallic source electrode consists of the first metal portion of the metallic source electrode overlying the second metal portion of the

metallic source electrode and the metallic drain electrode consists of the first metal portion of the metallic drain electrode overlying the second metal portion of the metallic drain electrode.

26. (Previously Presented) A transistor device as claimed in claim 1, wherein the metallic source, gate and drain electrodes consist entirely of electro-deposited material and the metallic gate electrode contacts the dielectric material.